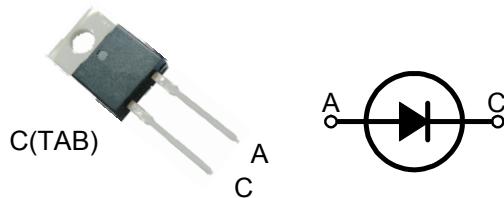


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## MUR1520-MUR1560

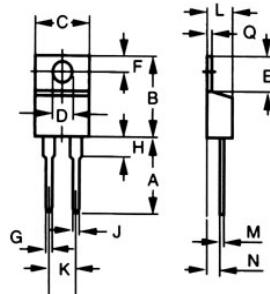
### Ultra Fast Recovery Diodes



A=Anode, C=Cathode, TAB=Cathode

	<b>V<sub>RSM</sub></b> <b>V</b>	<b>V<sub>RRM</sub></b> <b>V</b>
<b>MUR1520</b>	200	200
<b>MUR1540</b>	400	400
<b>MUR1560</b>	600	600

Dimensions TO-220AC



Dim.	Inches		Milimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.580	12.70	14.73
B	0.560	0.650	14.23	16.51
C	0.380	0.420	9.66	10.66
D	0.139	0.161	3.54	4.08
E	2.300	0.420	5.85	6.85
F	0.100	0.135	2.54	3.42
G	0.045	0.070	1.15	1.77
H	-	0.250	-	6.35
J	0.025	0.035	0.64	0.89
K	0.190	0.210	4.83	5.33
L	0.140	0.190	3.56	4.82
M	0.015	0.022	0.38	0.56
N	0.080	0.115	2.04	2.49
Q	0.025	0.055	0.64	1.39

Symbol	Test Conditions	Maximum Ratings			
		MUR1520	MUR1540	MUR1560	
I <sub>FRMS</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>	22	22	22	
I <sub>FAVM</sub>	T <sub>c</sub> =115°C; rectangular, d=0.5	15	15	15	
I <sub>FRM</sub>	t <sub>p</sub> <10us; rep. rating, pulse width limited by T <sub>VJM</sub>	170	170	170	A
I <sub>FSM</sub>	T <sub>VJ</sub> =45°C	250	230	210	A
	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	270	250	230	
I <sub>FSM</sub>	T <sub>VJ</sub> =150°C	190	170	150	A
	t=10ms(50Hz), sine t=8.3ms(60Hz), sine	210	190	170	
I <sup>2</sup> t	T <sub>VJ</sub> =45°C	50	50	50	A <sup>2</sup> s
	t=10ms (50Hz), sine t=8.3ms (60Hz), sine	50	50	50	
T <sub>VJ</sub>	T <sub>VJM</sub>	36	36	36	°C
	T <sub>stg</sub>	37	37	37	
P <sub>tot</sub>	T <sub>c</sub> =25°C	80			W
M <sub>d</sub>	Mounting torque	0.4...0.6			Nm
Weight		2			g



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## MUR1520-MUR1560

### Ultra Fast Recovery Diodes

Symbol	Test Conditions	Characteristic Values			
		MUR1520	MUR1540	MUR1560	Unit
I <sub>R</sub>	T <sub>VJ</sub> =25°C; V <sub>R</sub> =V <sub>RRM</sub> T <sub>VJ</sub> =25°C; V <sub>R</sub> =0.8·V <sub>RRM</sub> T <sub>VJ</sub> =125°C; V <sub>R</sub> =0.8·V <sub>RRM</sub>	20 10 1.5	20 10 1.5	20 10 1.5	uA uA mA
V <sub>F</sub>	I <sub>F</sub> =16A; T <sub>VJ</sub> =150°C T <sub>VJ</sub> =25°C	1.0 1.2	1.2 1.4	1.3 1.6	V
V <sub>TO</sub>	For power-loss calculations only	0.78	0.85	0.98	V
r <sub>T</sub>	T <sub>VJ</sub> =T <sub>VJM</sub>	25.5	27.8	28.7	mΩ
R <sub>thJC</sub> R <sub>thCK</sub> R <sub>thJA</sub>		2.5 0.5 60			K/W
t <sub>rr</sub>	I <sub>F</sub> =1A; -di/dt=50A/us; V <sub>R</sub> =30V; T <sub>VJ</sub> =25°C		35		ns
I <sub>RM</sub>	V <sub>R</sub> =350V; I <sub>F</sub> =8A; -di <sub>F</sub> /dt=64A/us; L≤0.05uH; T <sub>VJ</sub> =100°C		2.8		A

#### FEATURES

- \* International standard package JEDEC TO-220AC
- \* Planar passivated chips
- \* Very short recovery time
- \* Extremely low switching losses
- \* Low I<sub>RM</sub>-values

#### APPLICATIONS

- \* Antiparallel diode for high frequency switching devices
- \* Antisaturation diode
- \* Snubber diode
- \* Free wheeling diode in converters and motor control circuits
- \* Rectifiers in switch mode power supplies (SMPS)
- \* Inductive heating and melting
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

#### ADVANTAGES

- \* High reliability circuit operation
- \* Low voltage peaks for reduced protection circuits
- \* Low noise switching
- \* Low losses
- \* Operating at lower temperature or space saving by reduced cooling

